*# # + , - . / , 0 # 1 , 2 3 1 0 #

	F				
	F F		-4 625 mW 300mW		

##*## $, / 21.A<.3= /#

Silicon PNP transistor in a SOT-23 Plastic Package.

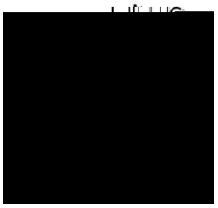
##*## 7 , :<B1 , /#

Complementary pair with L8050M.

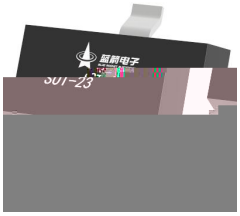
##*## %AA9.2 : <.3= /##

Power amplifier applications.

##*##) CB. - :9 , =<#8 .12B.<#



##*## D.==.=@#



PIN1 Base PIN 2 Emitter PIN 3 Collector

##*## $6_7)#89: / /.;.2 : <.3= /#>#" :1?.=@#

h_{FE}

#

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current - Continuous	I_C	-1.5	A
Base Current - Continuous	I_B	-0.5	A

Collector Po/ Ť L Dissi ī سخي o n n

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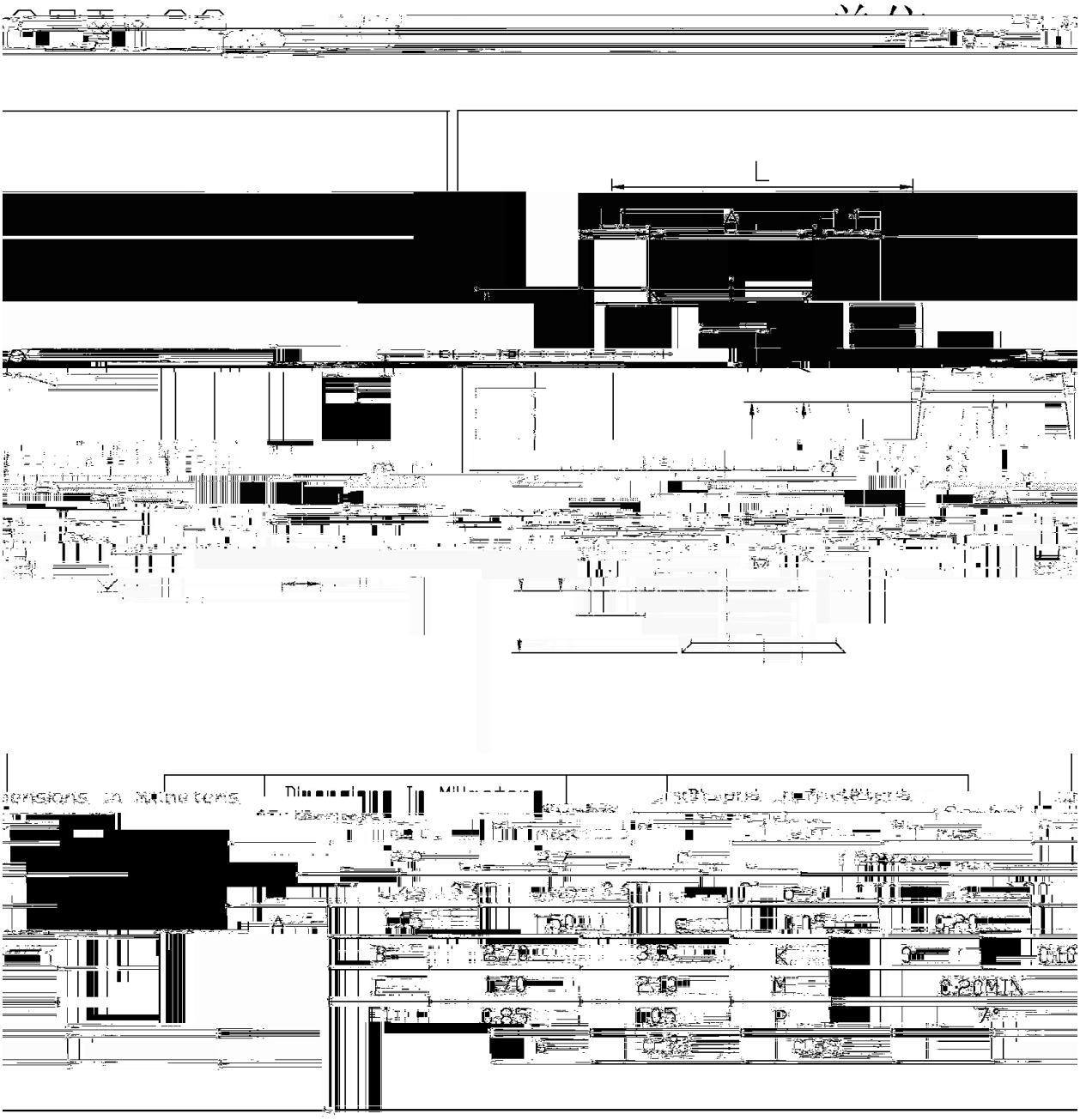
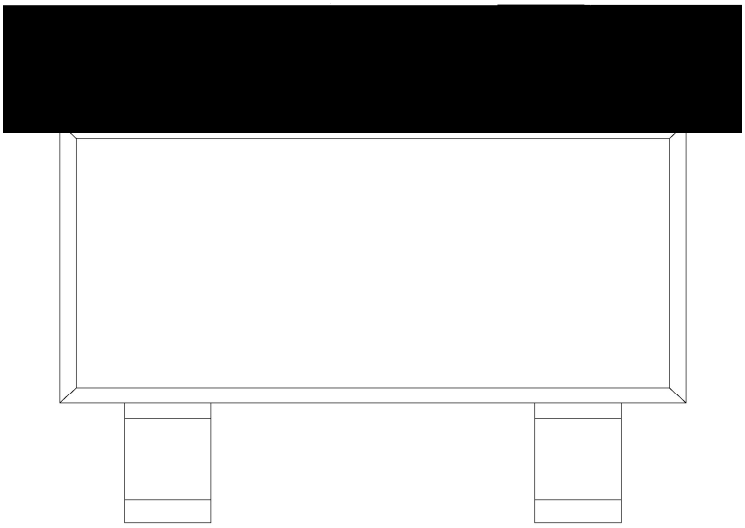
##*##D:2?:@,#$. I ,=/.3=/#



*# # " : 1 ? . = @ # N = / < 1 B 2 < . 3 = /



0

0

J L##*## Temperature Profile for IR Reflow Soldering(Pb-Free)

说明：

1、预热温度 150～180 ，时间 60～90sec;

2、峰值温度 245±5 ，时间持续为 5±0.5sec;

Note:

1.Preheating:150~180℃, Time:60~90sec.

2.Peak Temp.:245